

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	333	(aln or (aluminum adj nitride)) near carbon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:16
L4	5	(aln or (aluminum adj nitride)) near carbon near concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:16
S1	165	(nitride adj compound adj semiconductor) and (single adj crystal) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:15
S2	4	(nitride adj compound adj semiconductor) and (single adj crystal) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:16
S3	58	(nitride adj compound adj semiconductor) and (single adj crystal) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:49
S4	48	(nitride adj compound adj semiconductor) and (single adj crystalline) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:49
S5	1	(nitride adj compound adj semiconductor) and (single adj crystalline) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S6	15	(nitride adj compound adj semiconductor) and (single adj crystalline) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17

S7	3	(nitride adj compound adj semiconductor) and (mono adj crystal) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S8	0	(nitride adj compound adj semiconductor) and (mono adj crystal) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S9	1	(nitride adj compound adj semiconductor) and (mono adj crystal) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S10	31	(nitride adj compound adj semiconductor) and (monocrystal) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S11	0	(nitride adj compound adj semiconductor) and (monocrystal) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S12	12	(nitride adj compound adj semiconductor) and (monocrystal) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S13	2	(nitride adj compound adj semiconductor) and (mono adj crystalline) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S14	0	(nitride adj compound adj semiconductor) and (mono adj crystalline) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18

S15	3	(nitride adj compound adj semiconductor) and (mono adj crystalline) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S16	27	(nitride adj compound adj semiconductor) and (monocrystalline) and algan	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S17	3	(nitride adj compound adj semiconductor) and (monocrystalline) and alxga1-xn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S18	17	(nitride adj compound adj semiconductor) and (monocrystalline) and "al.sub.xga.sub.1-xn"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S19	143	(nitride adj compound adj semiconductor) and (single adj crystal) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:15
S20	4	(nitride adj compound adj semiconductor) and (single adj crystal) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:16
S21	55	(nitride adj compound adj semiconductor) and (single adj crystal) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:16
S22	44	(nitride adj compound adj semiconductor) and (single adj crystalline) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:13

S23	1	(nitride adj compound adj semiconductor) and (single adj crystalline) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S24	15	(nitride adj compound adj semiconductor) and (single adj crystalline) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S25	2	(nitride adj compound adj semiconductor) and (mono adj crystal) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S26	0	(nitride adj compound adj semiconductor) and (mono adj crystal) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:17
S27	1	(nitride adj compound adj semiconductor) and (mono adj crystal) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S28	31	(nitride adj compound adj semiconductor) and (monocrystal) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S29	0	(nitride adj compound adj semiconductor) and (monocrystal) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S30	12	(nitride adj compound adj semiconductor) and (monocrystal) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18

S31	2	(nitride adj compound adj semiconductor) and (mono adj crystalline) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S32	0	(nitride adj compound adj semiconductor) and (mono adj crystalline) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:18
S33	3	(nitride adj compound adj semiconductor) and (mono adj crystalline) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S34	27	(nitride adj compound adj semiconductor) and (monocrystalline) and algan and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S35	3	(nitride adj compound adj semiconductor) and (monocrystalline) and alxga1-xn and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S36	17	(nitride adj compound adj semiconductor) and (monocrystalline) and "al.sub.xga.sub.1-xn" and (aln or (aluminum adj nitride))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 00:19
S37	2	"5146465".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:44
S38	1	"5146465".pn. and crystal\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:36

S39	1	"5146465".pn. and thick\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/14 09:15
S40	1	"5146465".pn. and concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:41
S41	2	"6259122".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:44
S43	0	("al.sub.xga.sub.1-xn" or algan or alxga1-xn or (aluminum adj gallium adj nitride)) adj doped adj(c or carbon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:52
S44	0	("al.sub.xga.sub.1-xn" or algan or alxga1-xn or (aluminum adj gallium adj nitride)) adj doped adj (c or carbon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:52
S45	1	("al.sub.xga.sub.1-xn" or algan or alxga1-xn or (aluminum adj gallium adj nitride)) near doped near (c or carbon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 01:53
S46	118	("al.sub.xga.sub.1-xn" or algan or alxga1-xn or (aluminum adj gallium adj nitride)) with doped with (c or carbon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/14 06:37